## TOSHIBA

Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

# 2SK2949

#### Chopper Regulator, DC-DC Converter and Motor Drive Applications

- Low drain-source ON resistance  $: R_{DS} (ON) = 0.4 \Omega (typ.)$
- High forward transfer admittance  $|Y_{fs}| = 8.0 \text{ S (typ.)}$
- Low leakage current  $: IDSS = 100 \ \mu A \ (max) \ (VDS = 400 \ V)$
- Enhancement-mode :  $V_{th} = 2.0 \sim 4.0 \text{ V} (V_{DS} = 10 \text{ V}, \text{ ID} = 1 \text{ mA})$

#### Maximum Ratings (Ta = 25°C)

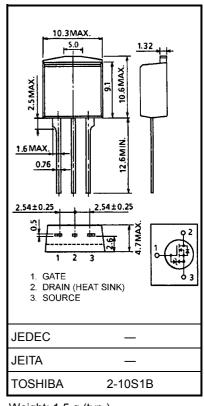
Characteris	stics	Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	400	V	
Drain-gate voltage (R	<sub>GS</sub> = 20 kΩ)	V <sub>DGR</sub>	400	V	
Gate-source voltage		V <sub>GSS</sub>	±30	V	
Drain current	DC (Note 1)	۱ <sub>D</sub>	10	А	
	Pulse (Note 1)	I <sub>DP</sub>	40	А	
Drain power dissipation	n (Tc = 25°C)	PD	80	W	
Single pulse avalanche energy (Note 2)		E <sub>AS</sub>	360	mJ	
Avalanche current		I <sub>AR</sub>	10	А	
Repetitive avalanche e	energy (Note 3)	E <sub>AR</sub>	8	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature ra	ange	T <sub>stg</sub>	-55~150	°C	

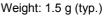
### **Thermal Characteristics**

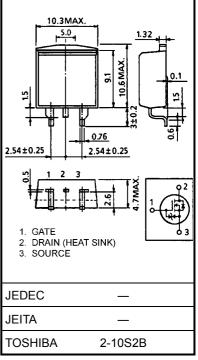
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R <sub>th (ch-c)</sub>	1.56	°C / W
Thermal resistance, channel to ambient	R <sub>th (ch−a)</sub>	83.3	°C / W

- Note 1: Please use devices on condition that the channel temperature is below 150°C.
- Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 5.85 mH,  $R_G$  = 25  $\Omega$ , I<sub>AR</sub> = 10 A
- Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.







Weight: 1.5 g (typ.)

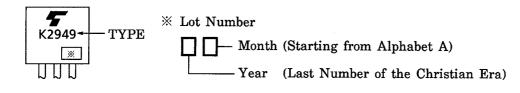
Electrical Characteristics (Ta = 25°C)

Charac	teristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	rrent	I <sub>GSS</sub>	$V_{GS}$ = ±25 V, $V_{DS}$ = 0 V	_	—	±10	μA
Gate-source bre	eakdown voltage	V (BR) GSS	$I_{G} = \pm 10 \ \mu A, V_{DS} = 0 \ V$	±30	_	_	V
Drain cut-off cu	rrent	I <sub>DSS</sub>	V <sub>DS</sub> = 400 V, V <sub>GS</sub> = 0 V		—	100	μA
Drain-source br	eakdown voltage	V (BR) DSS	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	400	_		V
Gate threshold v	voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	2.0	_	4.0	V
Drain-source O	N resistance	R <sub>DS (ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5.0 A		0.4	0.55	Ω
Forward transfer	admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 5.0 A	4.0	8.0		S
Input capacitance	e	C <sub>iss</sub>			1340		
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz		160		pF
Output capacitance		C <sub>oss</sub>			490		
Switching time	Rise time	tr	$V_{GS} \stackrel{10 \text{ V}}{_{0 \text{ V}}} \prod_{\substack{O \text{ V} \\ O \text{ C} \\ \downarrow \\ $	_	22	-	
	Turn-on time	t <sub>on</sub>		_	60	-	ns
	Fall time	t <sub>f</sub>		_	32	-	115
	Turn-off time	t <sub>off</sub>	Duty $\leq 1\%$ , t <sub>w</sub> = 10 µs	_	140	_	
Total gate charge (gate-source plus gate-drain)		Qg		_	34	_	
Gate-source charge		Q <sub>gs</sub>	V <sub>DD</sub> ≈ 320 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A		18	_	nC
Gate-drain ("miller") Charge		Q <sub>gd</sub>			16	—	

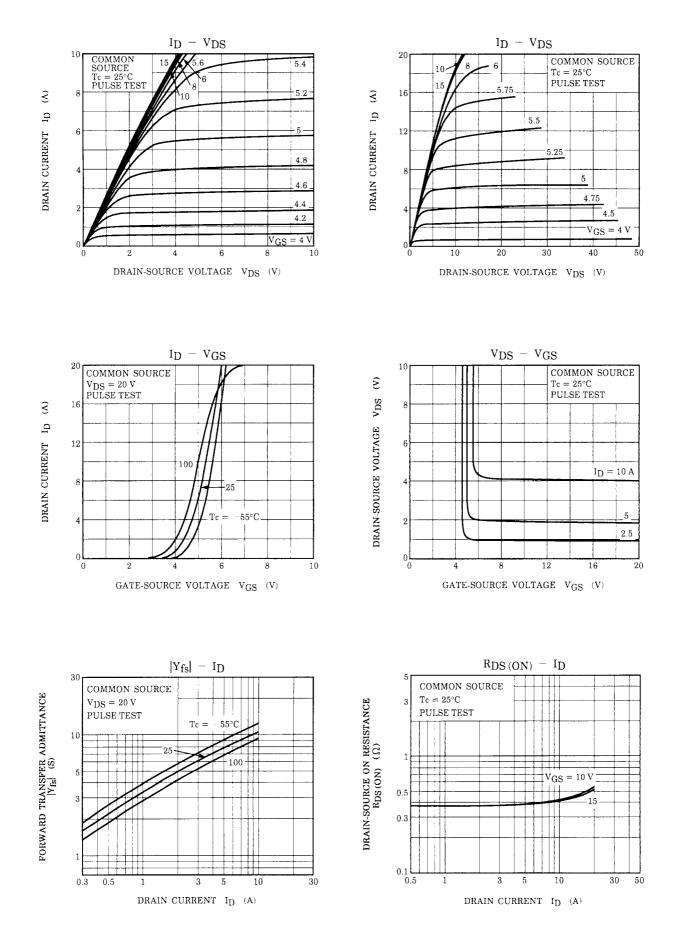
#### Source–Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>	—	_	_	10	А
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	—	_	_	40	А
Forward voltage (diode)	V <sub>DSF</sub>	I <sub>DR</sub> = 10 A, V <sub>GS</sub> = 0 V	_	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 10 A, V <sub>GS</sub> = 0 V		350		ns
Reverse recovery charge	Q <sub>rr</sub>	dI <sub>DR</sub> / dt = 100 Å / µs		2.6		μC

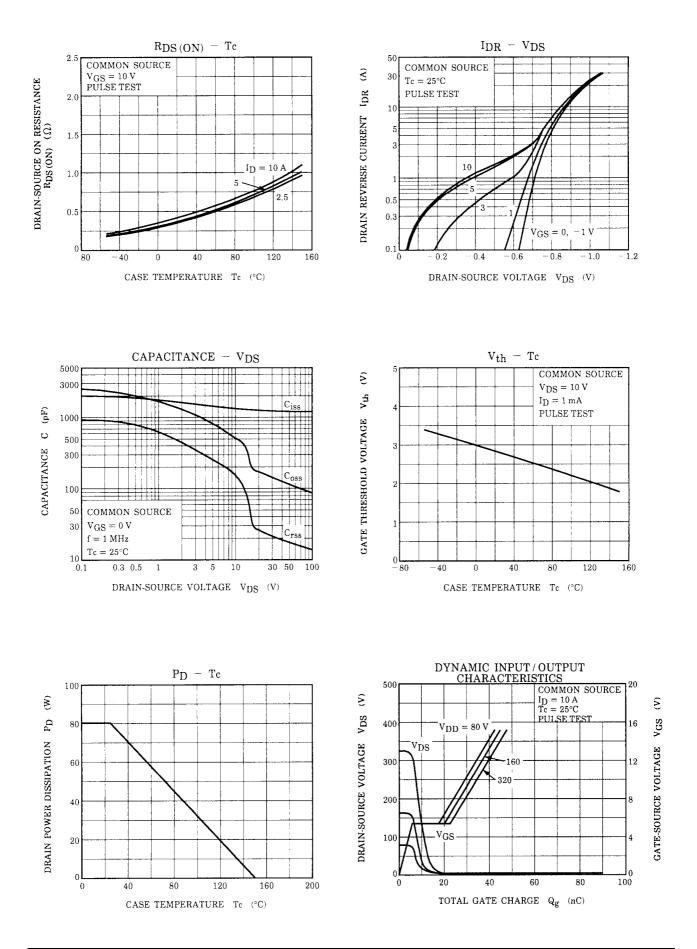
#### Marking

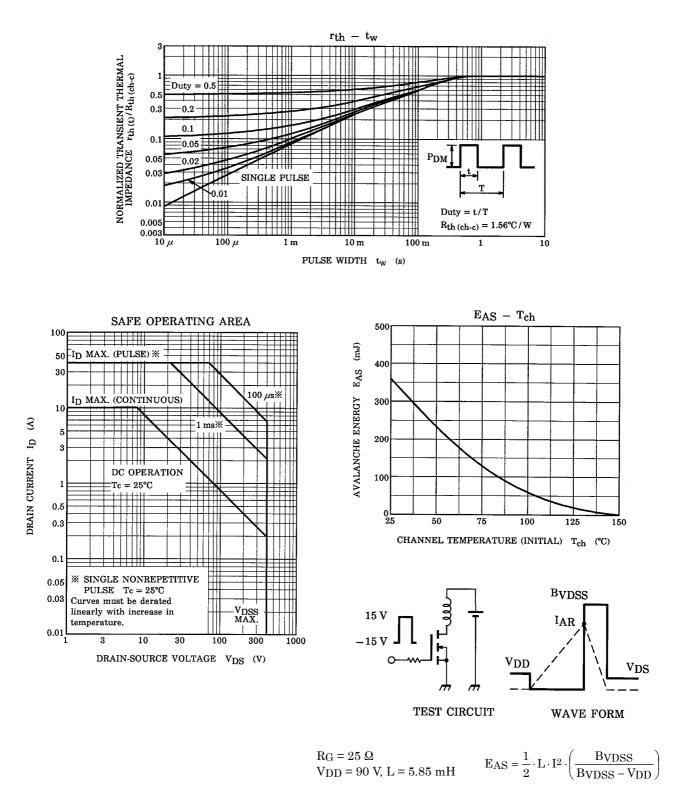


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